

MOSFETs Silicon N-channel MOS (U-MOSVII-H)

TPW5200FNH

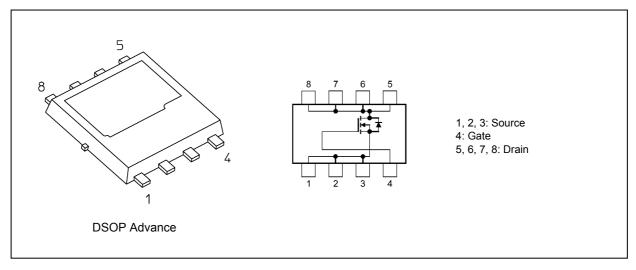
1. Applications

- · High-Efficiency DC-DC Converters
- Switching Voltage Regulators

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 8.2 \text{ nC (typ.)}$
- (3) Low drain-source on-resistance: $R_{DS(ON)}$ = 44 m Ω (typ.) (V_{GS} = 10 V)
- (4) Low leakage current: $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 250 \text{ V)}$
- (5) Enhancement mode: $V_{th} = 2.0 \text{ to } 4.0 \text{ V (V}_{DS} = 10 \text{ V}, I_D = 1.0 \text{ mA)}$

3. Packaging and Internal Circuit



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4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteris	stics		Symbol	Rating	Unit
Drain-source voltage			V_{DSS}	250	V
Gate-source voltage			V_{GSS}	±20	
Drain current (DC)	(T _c = 25 °C) (Bottom drain)	(Note 1)	Ι _D	26	А
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I _D	27]
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I_{DP}	105	
Power dissipation	(T _c = 25 °C) (Bottom drain)		P_{D}	142	W
Power dissipation		(Note 3)	P_{D}	2.5	1
Power dissipation		(Note 4)	P _D	0.8	
Single-pulse avalanche energy		(Note 5)	E _{AS}	103	mJ
Single-pulse avalanche current		(Note 5)	I _{AS}	26	Α
Channel temperature			T _{ch}	150	°C
Storage temperature			T _{stg}	-55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristic	Symbol	Max	Unit		
Channel-to-case thermal resistance	Bottom drain (T _c = 25 °C)		R _{th(ch-c)}	0.88	°C/W
Channel-to-case thermal resistance	Top source (T _c = 25 °C)		R _{th(ch-c)}	0.93	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 3)	R _{th(ch-a)}	50	°C/W
Channel-to-ambient thermal resistance	(T _a = 25 °C)	(Note 4)	R _{th(ch-a)}	156	°C/W

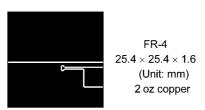
Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Limited by silicon chip capability.

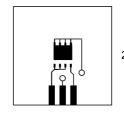
Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 60 V, T_{ch} = 25 °C (initial), L = 250 μ H, I_{AS} = 26 A







FR-4 25.4 × 25.4 × 1.6 (Unit: mm) 2 oz copper

Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μΑ
Drain cut-off current	I _{DSS}	V _{DS} = 250 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	250	_	_	V
	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	175	_	_	
Gate threshold voltage	V_{th}	V _{DS} = 10 V, I _D = 1.0 mA	2.0	_	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 13 A	_	44	52	mΩ

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 100 V, V _{GS} = 0 V, f = 1 MHz	_	1700	2200	pF
Reverse transfer capacitance	C _{rss}		_	7.0	50	
Output capacitance	C _{oss}		_	140		
Gate resistance	r _g	_	_	4.0	6.0	Ω
Switching time (rise time)	t _r	See Fig. 6.2.1	_	8.0		ns
Switching time (turn-on time)	t _{on}		_	20	_	
Switching time (fall time)	t _f		_	12	_	
Switching time (turn-off time)	t _{off}		_	36		

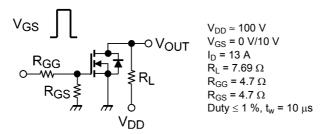


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (Ta = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	$V_{DD} \approx 100 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 26 \text{ A}$	1	22	ı	nC
Gate-source charge 1	Q _{gs1}		_	9.0		nC
Gate-drain charge	Q_{gd}		_	4.4		
Gate switch charge	Q_{SW}		_	8.2	_	

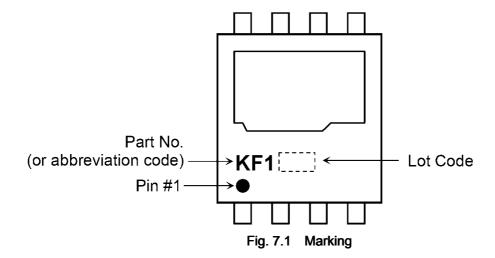
6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 6)	I _{DRP}	_	_	_	105	Α
Diode forward voltage	V _{DSF}	I _{DR} = 26 A, V _{GS} = 0 V			-1.2	V
Reverse recovery time	t _{rr}	V _{DD} = 125 V, I _{DR} = 6.5 A,	_	110		ns
Reverse recovery charge	Q _{rr}	$V_{GS} = 0 \text{ V}, -dI_{DR}/dt = 100 \text{ A/}\mu\text{s}$	_	420	_	nC

Note 6: Ensure that the channel temperature does not exceed 150 °C.



7. Marking



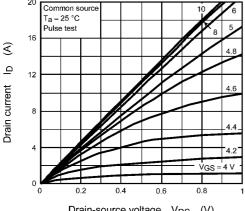


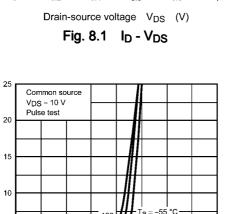
€

₽

Drain current

8. Characteristics Curves (Note)





 $\label{eq:Gate-source} \begin{array}{ccc} \text{Gate-source voltage} & \text{V}_{GS} & \text{(V)} \\ & \textbf{Fig. 8.3} & \textbf{I}_{\textbf{D}} \textbf{-} \textbf{V}_{\textbf{GS}} \end{array}$

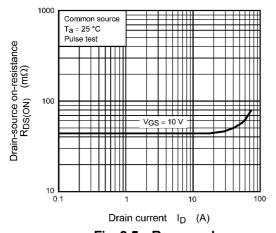


Fig. 8.5 R_{DS(ON)} - I_D

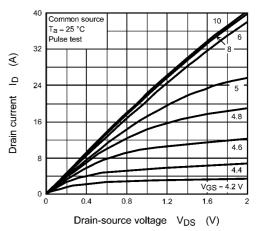


Fig. 8.2 I_D - V_{DS}

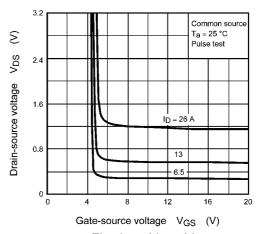


Fig. 8.4 $V_{DS} - V_{GS}$

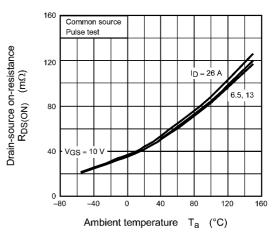


Fig. 8.6 R_{DS(ON)} - T_a



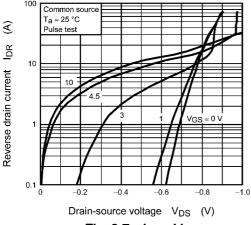


Fig. 8.7 IDR - VDS

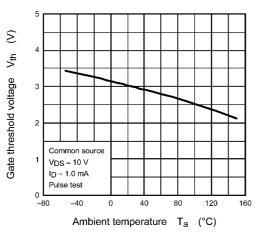


Fig. 8.9 Vth - Ta

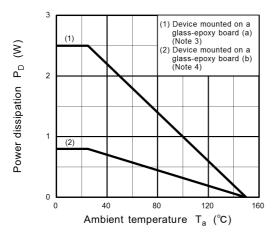


Fig. 8.11 P_D - T_a (Guaranteed Maximum)

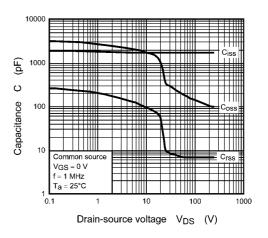


Fig. 8.8 Capacitance - V_{DS}

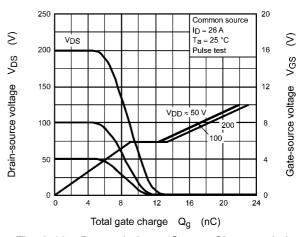


Fig. 8.10 Dynamic Input/Output Characteristics

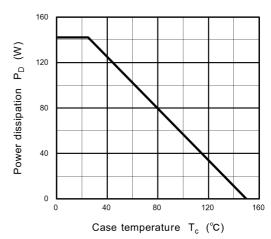


Fig. 8.12 P_D - T_c (Bottom drain) (Guaranteed Maximum)



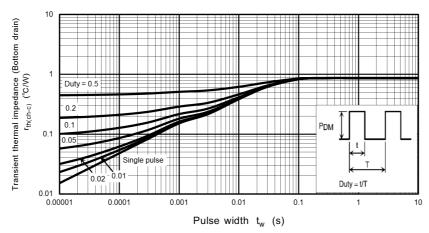


Fig. 8.13 r_{th} - t_w (Bottom drain) (Guaranteed Maximum)

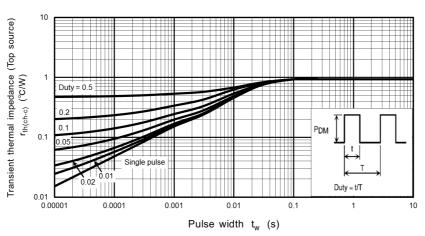


Fig. 8.14 r_{th} - t_w (Top source) (Guaranteed Maximum)

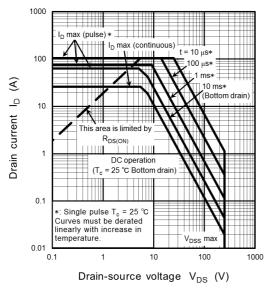


Fig. 8.15 Safe Operating Area (Guaranteed Maximum)



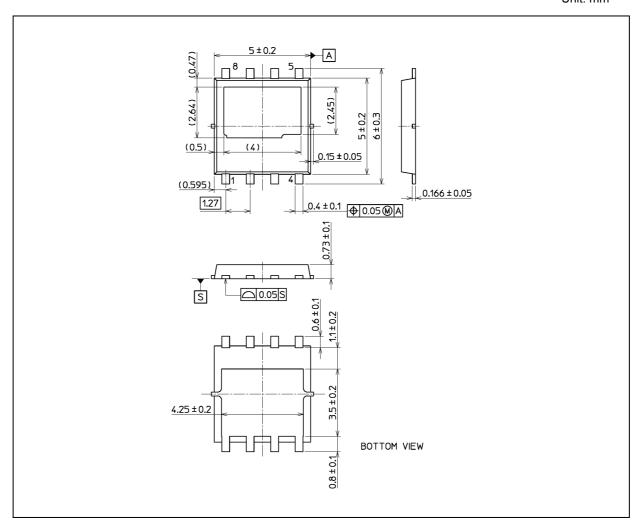
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Rev.3.0



Package Dimensions

Unit: mm



Weight: 0.104 g (typ.)

Package Name(s)
TOSHIBA: 2-5S1A
Nickname: DSOP Advance

Rev.3.0



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